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Preferred Devices

Thyristor Surge Protectors

High Voltage Bidirectional TSPD

These Thyristor Surge Protective devices (TSPD) prevent overvoltage damage to sensitive circuits by lightning, induction and power line crossings. They are breakover-triggered crowbar protectors. Turn-off occurs when the surge current falls below the holding current value.

- High Surge Current Capability: 80 Amps 10 x 1000 µsec, for **Controlled Temperature Environments**
- The MMT08B310 is used to help equipment meet various regulatory requirements including: Bellcore 1089, ITU K.20 & K.21, IEC 950, UL 1459 & 1950 and FCC Part 68.
- Bidirectional Protection in a Single Device
- Little Change of Voltage Limit with Transient Amplitude or Rate
- Freedom from Wearout Mechanisms Present in Non-Semiconductor Devices
- Fail-Safe, Shorts When Overstressed, Preventing Continued **Unprotected Operation**
- Surface Mount Technology (SMT)
- 91 Indicates UL Registered - File #E210057
- Pb-Free Package is Available

MAXIMUM RATINGS (T₁ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Off-State Voltage - Maximum MMT08B310T3	V _{DM}	±270	V
Maximum Pulse Surge Short Circuit Current Non–Repetitive Double Exponential Decay Waveform (Notes 1 and 2) 10 x 1000 μsec (–25°C Initial Temperature) 8 x 20 μsec 10 x 160 μsec 10 x 560 μsec	IPPS1 IPPS2 IPPS3 IPPS4	±80 ±250 ±150 ±100	A(pk)
$\begin{array}{l} \mbox{Maximum Non-Repetitive Rate of} \\ \mbox{Change of On-State Current} \\ \mbox{Double Exponential Waveform,} \\ \mbox{R} = 1.0, \mbox{L} = 1.5 \ \mu\mbox{H}, \mbox{C} = 1.67 \ \mu\mbox{F}, \\ \mbox{I}_{pk} = 110\mbox{A} \end{array}$	di/dt	±150	A/μs

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

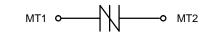
- 1. Allow cooling before testing second polarity.
- 2. Measured under pulse conditions to reduce heating.



ON Semiconductor®

http://onsemi.com

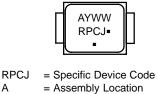
BIDIRECTIONAL TSPD (9) **80 AMP SURGE 310 VOLTS**





SMB (No Polarity) (Essentially JEDEC DO-214AA) CASE 403C

MARKING DIAGRAM



= Year

= Work Week

A Y

WW

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MMT08B310T3	SMB	2500 Tape & Reel
MMT08B310T3G	SMB Pb-Free	2500 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Operating Temperature Range Blocking or Conducting State	T _{J1}	-40 to +125	°C
Overload Junction Temperature – Maximum Conducting State Only	T _{J2}	+175	°C
Instantaneous Peak Power Dissipation (I _{pk} = 50 A, 10x1000 µsec @ 25°C)	P _{PK}	2000	W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

ELECTRICAL CHARACTERISTICS (T_J = $25^{\circ}C$ unless otherwise noted)

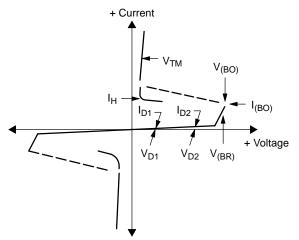
Devices are bidirectional. All electrical parameters apply to forward and reverse polarities.

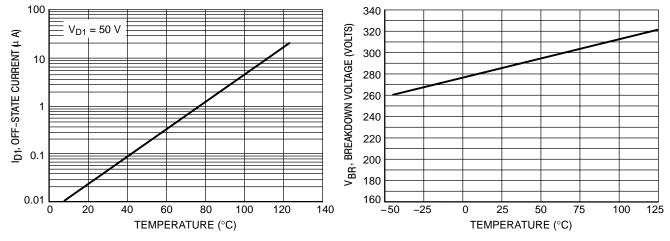
Characteristics		Symbol	Min	Тур	Max	Unit
Breakover Voltage (Both polarities) (dv/dt = 100 V/μs, I _{SC} = 1.0 A, Vdc = 1000 V) (+65°C)	MMT08B310T3	V _(BO)	_	_	365	V
(100 0)	MMT08B310T3		-	-	400	
Breakover Voltage (Both polarities)		V _(BO)				V
(f = 60 Hz, I _{SC} = 1.0 A(rms), V _{OC} = 1000 V(rms), R _I = 1.0 kΩ, t = 0.5 cycle) (Note 3) (+65°C)	MMT08B310T3		-	_	365	
(100 0)	MMT08B310T3		-	-	400	
Breakover Voltage Temperature Coefficient		dV _(BO) /dT _J	-	0.08	_	%/°C
Breakdown Voltage ($I_{(BR)}$ = 1.0 mA) Both polarities	MMT08B310T3	V _(BR)	-	310	-	V
Off State Current ($V_{D1} = 50 \text{ V}$) Both polarities ($V_{D2} = V_{DM}$) Both polarities		I _{D1} I _{D2}			2.0 5.0	μA
On–State Voltage ($I_T = 1.0 \text{ A}$) (PW $\leq 300 \ \mu\text{s}$, Duty Cycle $\leq 2\%$) (Note 3)		VT	-	1.53	3.0	V
Breakover Current (f = 60 Hz, V_{DM} = 1000 V(rms), R_S = 1.0 k Ω) Both polarities		I _{BO}	-	230	-	mA
Holding Current (Both polarities) $V_S = 500$ Volts; I _T (Initiating Current) = ± 1.0 Amp	(Note 3)	I _Н	150	340	-	mA
Critical Rate of Rise of Off–State Voltage (Linear waveform, V_D = Rated V_{BR} , T_J = 25°C)		dv/dt	2000	-	-	V/µs
Capacitance (f = 1.0 MHz, 50 Vdc, 1.0 V rms Signal) (f = 1.0 MHz, 2.0 Vdc, 1.0 V rms Signal)		Co		23 -	25 50	pF

3. Measured under pulse conditions to reduce heating.

Voltage Current Characteristic of TSPD (Bidirectional Device)

Symbol	Parameter	
I _{D1} , I _{D2}	Off State Leakage Current	
V _{D1} , V _{D2}	Off State Blocking Voltage	
V _{BR}	Breakdown Voltage	
V _{BO}	Breakover Voltage	
I _{BO}	Breakover Current	
Ι _Η	Holding Current	
V _{TM}	On State Voltage	





1000

900

800

700

600

Figure 1. Off-State Current versus Temperature

Figure 2. Breakdown Voltage versus Temperature

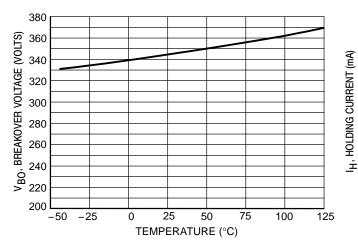


Figure 3. Breakover Voltage versus Temperature

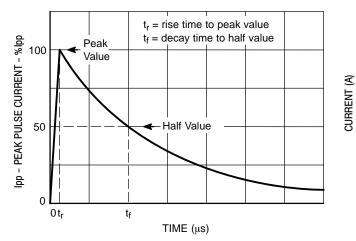


Figure 5. Exponential Decay Pulse Waveform

500 400 300 200 100 -50 -25 0 25 50 75 100 125 TEMPERATURE (°C)

Figure 4. Holding Current versus Temperature

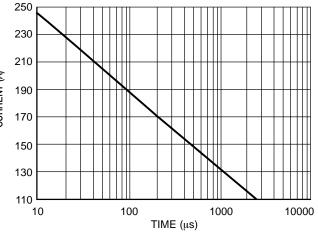
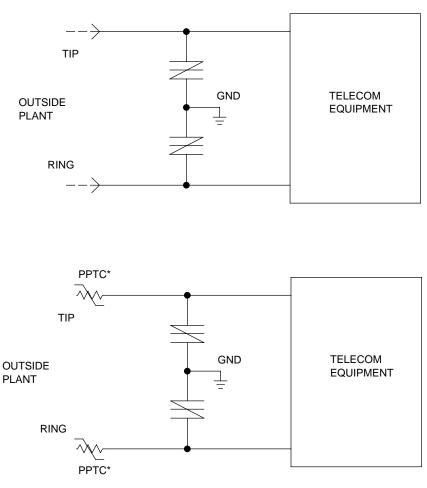
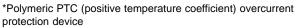
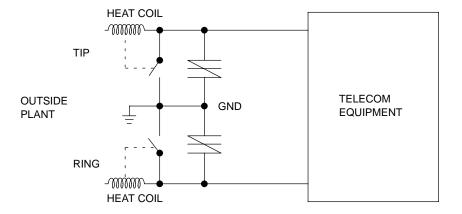


Figure 6. Peak Surge On–State Current versus Surge Current Duration, Sinusoidal Waveform

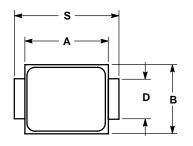






PACKAGE DIMENSIONS

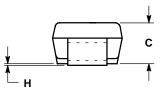
SMB (No Polarity) (Essentially JEDEC DO-214AA) CASE 403C-01 **ISSUE A**



κ

J

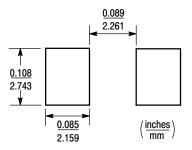
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NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.160	0.180	4.06	4.57	
В	0.130	0.150	3.30	3.81	
С	0.075	0.095	1.90	2.41	
D	0.077	0.083	1.96	2.11	
Н	0.0020	0.0060	0.051	0.152	
J	0.006	0.012	0.15	0.30	
Κ	0.030	0.050	0.76	1.27	
Р	0.020 REF		0.51	REF	
S	0.205	0.220	5.21	5.59	

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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